NSDEMN11XV6T1, NSDEMN11XV6T5

Common Cathode Quad Array Switching Diode

This Common Cathode Epitaxial Planar Quad Diode is designed for use in ultra high speed switching applications. This device is housed in the SOT–563 package which is designed for low power surface mount applications, where board space is at a premium.

Features

- Fast t_{rr}
- Low C_D
- Pb-Free Packages are Available

MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

Rating	Symbol	Value	Unit
Reverse Voltage	V _R	80	Vdc
Peak Reverse Voltage	V _{RM}	80	Vdc
Forward Current	Ι _F	100	mAdc
Peak Forward Current	I _{FM}	300	mAdc
Peak Forward Surge Current	I _{FSM} (Note 1)	2.0	Adc

THERMAL CHARACTERISTICS

Characteristic (One Junction Heated)	Symbol	Max	Unit
Total Device Dissipation @T _A = 25°C Derate above 25°C	P _D	357 (Note 2) 2.9 (Note 2)	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	350 (Note 2)	°C/W
Characteristic (Both Junctions Heated)	Symbol	Max	Unit
Total Device Dissipation @T _A = 25°C Derate above 25°C	P _D	500 (Note 2) 4.0 (Note 2)	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	250 (Note 2)	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

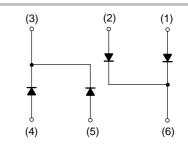
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. $t = 1 \mu S$
- 2. FR-4 @ Minimum Pad



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SOT-563 CASE 463A PLASTIC

MARKING DIAGRAM



N9 = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
NSDEMN11XV6T1	SOT-563	4000/Tape & Reel
NSDEMN11XV6T1G	SOT-563 (Pb-Free)	4000/Tape & Reel
NSDEMN11XV6T5	SOT-563	8000/Tape & Reel
NSDEMN11XV6T5G	SOT-563 (Pb-Free)	8000/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NSDEMN11XV6T1, NSDEMN11XV6T5

ELECTRICAL CHARACTERISTICS (T_A = 25°C)

Characteristic	Symbol	Condition	Min	Max	Unit
Reverse Voltage Leakage Current	I _R	V _R = 70 V	-	0.1	μAdc
Forward Voltage	V _F	I _F = 100 mA	_	1.2	Vdc
Reverse Breakdown Voltage	V _R	I _R = 100 μA	80	_	Vdc
Diode Capacitance	C _D	V _R = 6.0 V, f = 1.0 MHz	_	3.5	pF
Reverse Recovery Time	t _{rr} (Note 3)	I_F = 5.0 mA, V_R = 6.0 V, R_L = 100 Ω , I_{rr} = 0.1 I_R	1	4.0	ns

^{3.} t_{rr} Test Circuit on following page.

TYPICAL ELECTRICAL CHARACTERISTICS

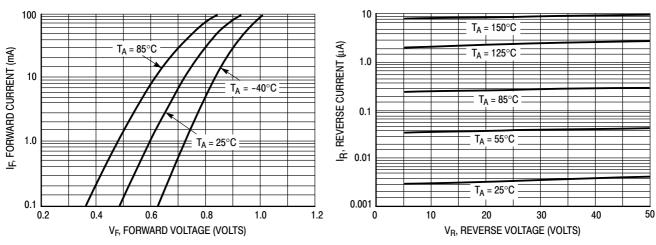


Figure 1. Forward Voltage

Figure 2. Reverse Current

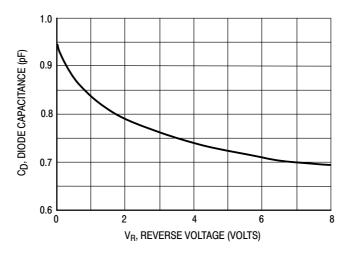


Figure 3. Diode Capacitance

NSDEMN11XV6T1, NSDEMN11XV6T5

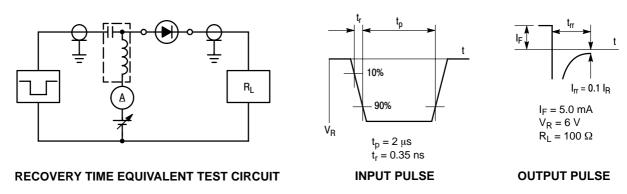


Figure 4. Reverse Recovery Time Test Circuit for the NSDEMN11XV6T1



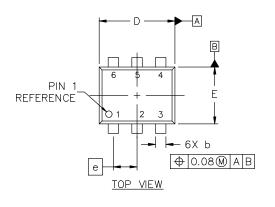


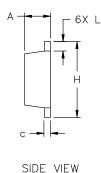
SOT-563-6 1.60x1.20x0.55, 0.50P CASE 463A **ISSUE J**

DATE 15 FEB 2024

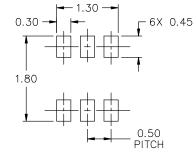
NOTES:

- DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
- ALL DIMENSION ARE IN MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.





DIM	MILLIMETERS		:RS
ויונע	MIN.	N□M.	MAX.
А	0.50	0.55	0.60
b	0.17	0.22	0.27
C	0.08	0.13	0.18
D	1.50	1.60	1.70
E	1.10	1.20	1.30
е	0.50 BSC		
Н	1.50	1.60	1.70
L	0.10	0.20	0.30



STYLE 1:	STYLE 2:	STYLE 3:
PIN 1. EMITTER 1	PIN 1. EMITTER 1	PIN 1. CATHODE 1
2. BASE 1	2. EMITTER 2	2. CATHODE 1
3. COLLECTOR 2	3. BASE 2	3. ANODE/ANODE 2
4. EMITTER 2	4. COLLECTOR 2	4. CATHODE 2
5. BASE 2	5. BASE 1	5. CATHODE 2
6. COLLECTOR 1	6. COLLECTOR 1	6. AN□DE/AN□DE 1

STYLE 6: PIN 1. CATHODE 2. ANODE

SOT-563-6 1.60x1.20x0.55, 0.50P

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3. CATHODE 4. CATHODE 5. CATHODE

RECOMMENDED	MOLINITING	FOOTPRINT*
KECOMIMENDED	MOONTING	LOO INKINI.

FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

STYLE 7:	STYLE 9: PIN 1. SDURCE 1 2. GATE 1 3. DRAIN 2 4. SDURCE 2 5. GATE 2 6. DRAIN 1
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STYLE 5:

PIN 1. CATHODE

2. CATHODE

3. ANDDE 4. ANDDE 5. CATHODE

GENERIC MARKING DIAGRAM*



XX = Specific Device Code M = Month Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

STYLE 10:	STYLE 11:
PIN 1. CATHODE 1	PIN 1. EMITTER 2
2. N/C	2. BASE 2
3. CATHODE 2	3. COLLECTOR 1
4. AN□DE 2	4. EMITTER 1
5. N/C	5. BASE 1
6. AN□DE 1	6. COLLECTOR 2

STYLE 4: PIN 1. COLLECTOR

2. COLLECTOR

3. BASE 4. EMITTER 5. COLLECTOR

COLLECTOR

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DESCRIPTION:

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